Ordering number : EN1872A

SANYO No. 1872A

DRA2T

Silicon Planar Type

2.0A Reverse Blocking Thyristor

Features

- TO202 package facilitating easy mounting
- Peak OFF-state (reverse) voltage : −100 to −600V
- Average ON-state current : 2A

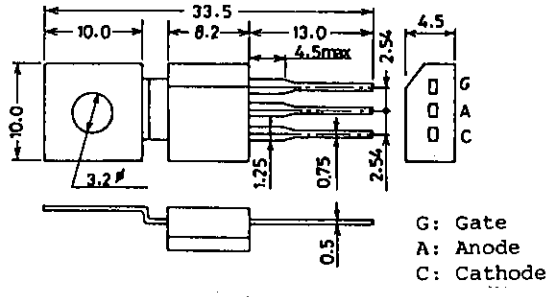
Absolute Maximum Ratings at Ta=25°C

			DRA2TB	DRA2TC	DRA2TE	DRA2TG	unit
Repetitive Peak OFF-State Voltage	V_{DRM}	R_{GK}=1kΩ	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	R_{GK}=1kΩ	−150	−300	−500	−720	V
Repetitive Peak Reverse Voltage	V_{RRM}	R_{GK}=1kΩ	−100	−200	−400	−600	V
Average ON-State Current	$I_{T(AV)}$	Tc=45°C, single-phase half-wave	→	→	→	2	A
Surge ON-State Current	I_{TSM}	Sine half-wave 1 cycle, 50Hz	→	→	→	20	A
Amperes Squared-Seconds	$\int i^2T \cdot dt$	1ms≦t≦10ms	→	→	→	1.6	A^2s
Peak Gate Power Dissipation	P_{GM}	f≧50Hz,duty≦10%	→	→		0.1	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	→	0.01	W
Peak Gate Forward Current	I_{FGM}	f≧50Hz,duty≦10%	→	→	→	0.1	A
Peak Gate Reverse Voltage	V_{RGM}		→	→	→	−5	V
Junction Temperature	Tj		→	→	→	110	°C
Storage Temperature	Tstg		→	→		−40 to +110	°C
Weight			→	→	→	1.5	g

Electrical Characteristics at Ta=25°C

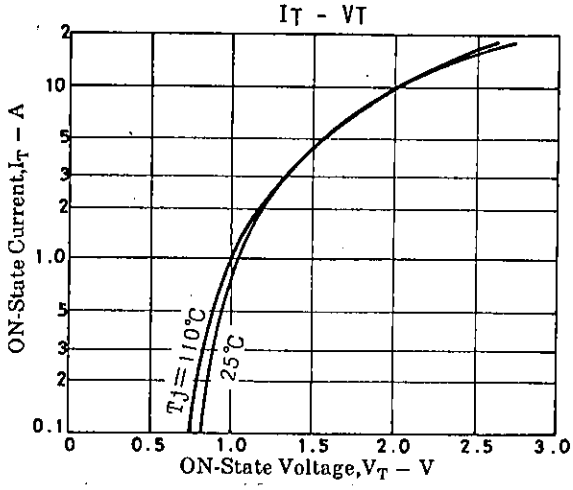
			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	Tj=110°C,V_D=V_{DRM},R_{GK}=1kΩ			0.2	mA
Repetitive Peak Reverse Current	I_{RRM}	Tj=110°C,V_R=V_{RRM},R_{GK}=1kΩ			−0.2	mA
Peak ON-State Voltage	V_{TM}	I_{TM}=10A			2.0	V
Critical Rate of Rise of OFF-State Voltage	dv/dt	Tj=110°C,V_D=V_{DRM},R_{GK}=1kΩ		15 10(G)		V/μs
Holding Current	I_H	V_D=24V,R_{GK}=1kΩ		3.0		mA
Gate Trigger Current	I_{GT}	V_D=6V,R_L=100Ω,R_{GK}=1kΩ			0.2	mA
Gate Trigger Voltage	V_{GT}	V_D=6V,R_L=100Ω,R_{GK}=1kΩ			0.8	V
Gate Nontrigger Voltage	V_{GD}	Tc=110°C,V_D=Rated voltage,R_{GK}=1kΩ	0.2			V
Thermal Resistance	Rth(j−c)				12	°C/W

Package Dimensions 1150
(unit: mm)

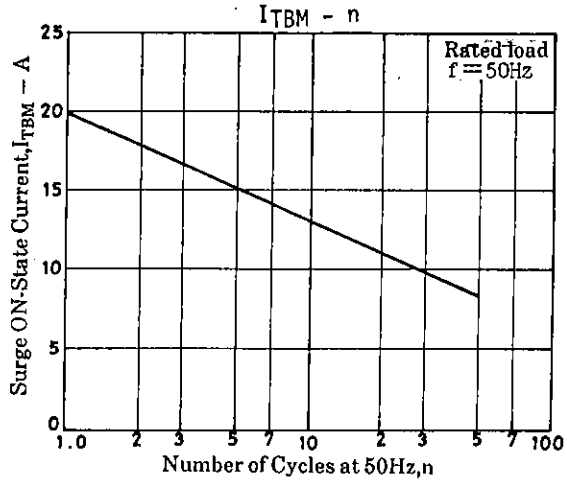


SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg.,1-10,1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

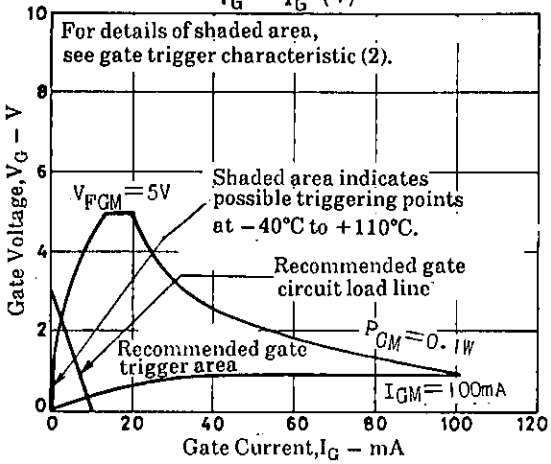
I_T - V_T



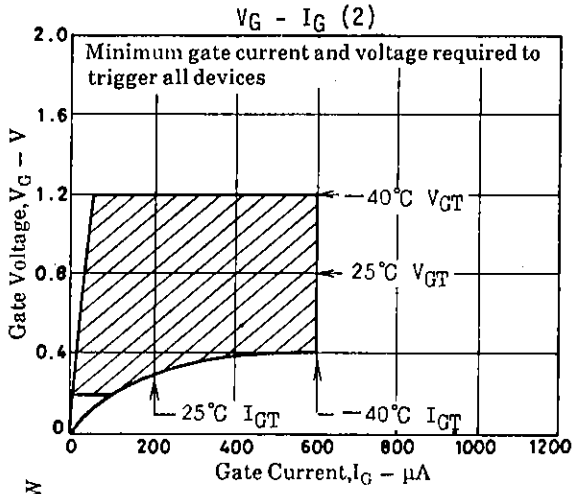
I_{TBM} - n



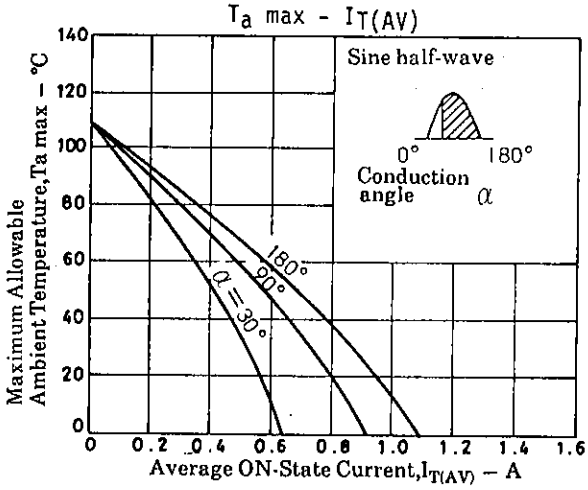
V_G - I_G (1)



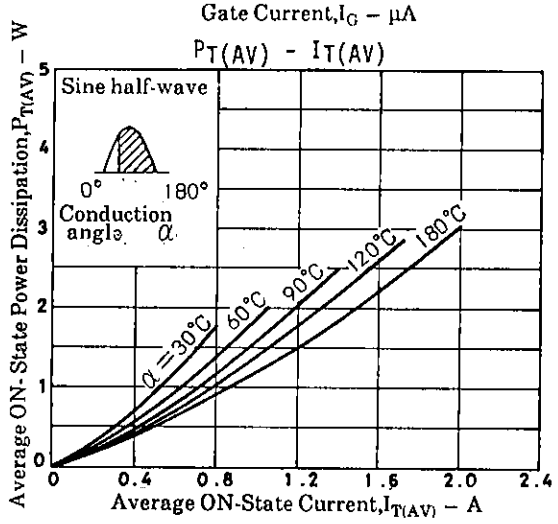
V_G - I_G (2)



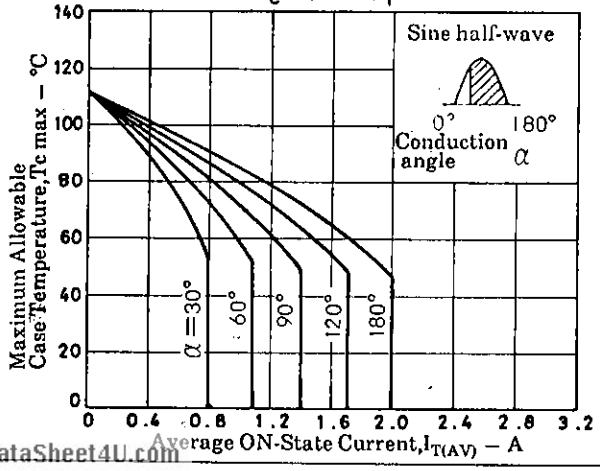
T_a max - $I_{T(AV)}$



$P_{T(AV)}$ - $I_{T(AV)}$



T_C max - I_T



I_{GT} - T_C